

## Supplementary Information

### **Composition-dependent Photoconductivities in Indium Aluminium Nitride Nanorods Grown by Magnetron Sputter Epitaxy**

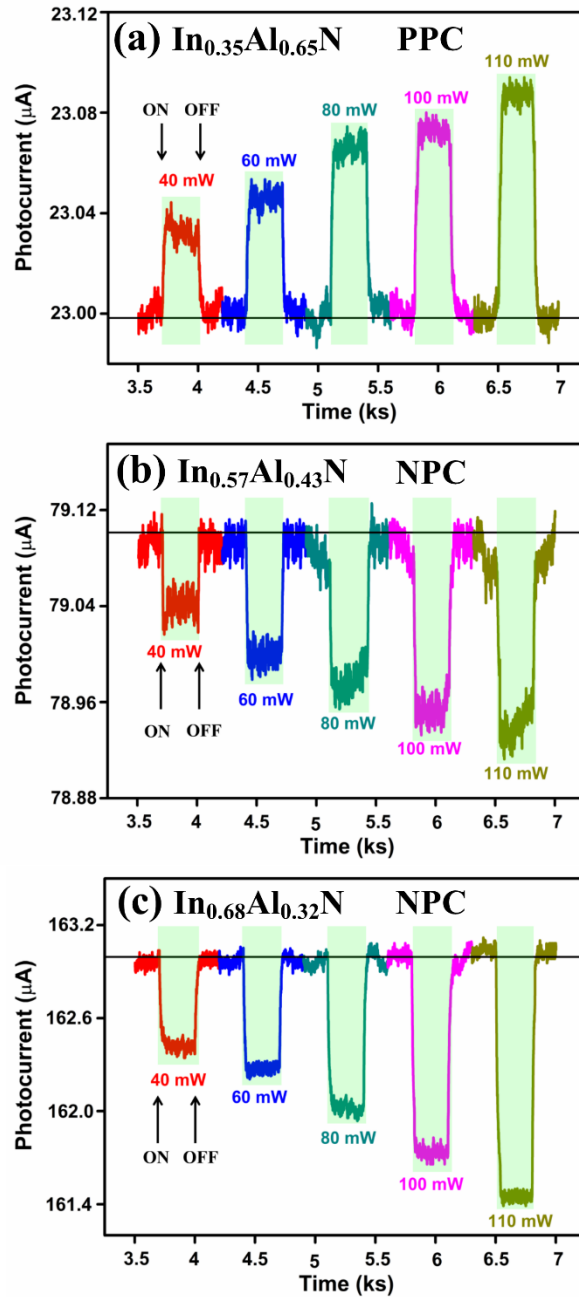
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**Supplementary Figure 1.** Photocurrent response measurements of  $\text{In}_x\text{Al}_{1-x}\text{N}$  NR devices under different powers of green light illumination with the wavelength of 532 nm. The photocurrent measurements include dark current.